TOSHIBA

TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

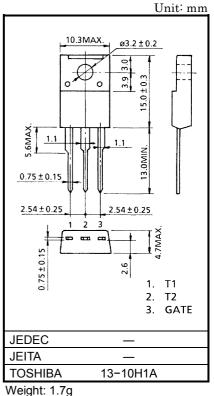
SM12GZ47,SM12JZ47,SM12GZ47A,SM12JZ47A

AC POWER CONTROL APPLICATIONS

- Repetitive Peak off-State Voltage : V_{DRM} = 400, 600V
- R.M.S On-State Current •
- : IT (RMS) = 12A
- High Commutating (dv / dt) •
- Isolation Voltage
- $: V_{Isol} = 1500 V AC$

MAXIMUM RATINGS

CHARACTERI	SYMBOL	RATING	UNIT		
Repetitive Peak Off-State Voltage and	SM12GZ47 SM12GZ47A	Vaav	400	V	
Repetitive Peak Reverse Voltage	SM12JZ47 SM12JZ47A	V _{DRM}	600	v	
R. M. S. On-tate Current (Full Sine Waveform TC = 72°C)		I _{T (RMS)}	12	А	
Peak One Cylce Surge On-State Current (Non-Repetitive)		I _{TSM}	120 (50Hz)	Α	
			132 (60Hz)	A	
I ² t Limit Value		l ² t	72	A ² s	
Critical Rate of Rise of On-State Current (Note 1)		di / dt	50	Α / μs	
Peak Gate Power Dissip	ation	P _{GM}	5	W	
Average Gate Power Dis	ssipation	P _{G (AV)}	0.5	W	
Peak Gate Voltage		V _{FGM}	10	V	
Peak Gate Current		I _{GM}	2	А	
Junction Temperature		Tj	-40~125	°C	
Storage Temperature R	ange	T _{stg}	-40~125	°C	
Isolation Voltage (AC, t	= 1min.)	V _{Isol}	1500	V	



Note 1: di / dt test condition V_{DRM} = 0.5 × Rated $I_{TM} \le 17A$ t_{qw} ≥ 10µs t_{gr} ≤ 250ns $i_{gp} = I_{GT} \times 2.0$

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

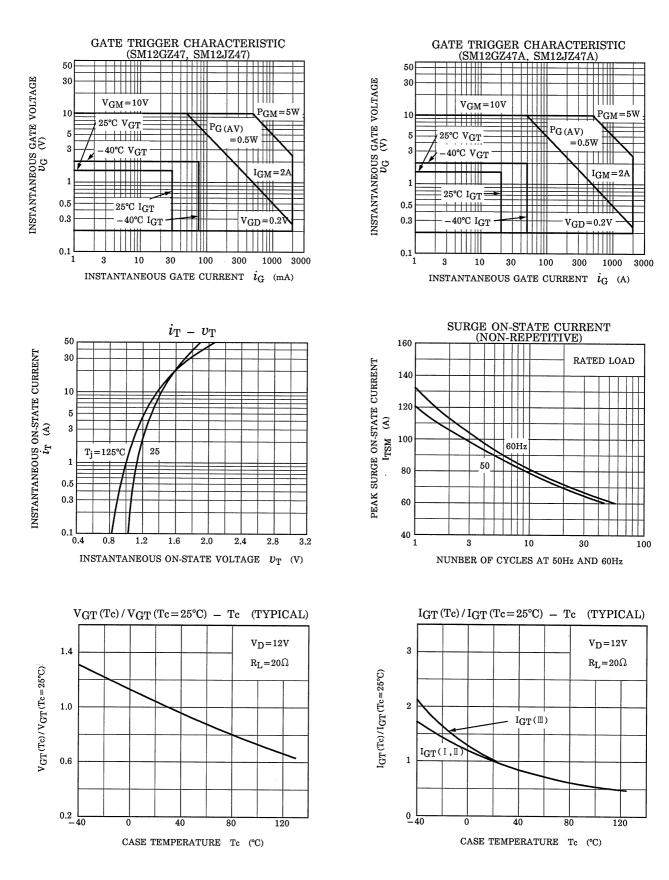
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT		
Repetitive Peak	Off−Sta	te Current		IDRM	V _{DRM} = Rated			—	20	μA
			Ι	- V _{GT}	V _D = 12V,	T2 (+) , Gate (+)	_	_	1.5	V
Coto Triagor Vol			П			T2 (+) , Gate (−)	-	_	1.5	
Gate mgger von			Ш	VGT	R _L = 20Ω	T2 (-) , Gate (-)		_	1.5	
			IV			T2 (-) , Gate (+)		_	_	
			I			T2 (+) , Gate (+)		_	30	
	SM12	GZ47	П			T2 (+) , Gate (−)		_	30	
Gate Trigger Current	JZ47	Ш		V _D = 12V, R _L = 20Ω	T2 (-) , Gate (-)		_	30	mA	
		IV			T2 (-) , Gate (+)		_	_		
		Ι	I _{GT}		T2 (+) , Gate (+)	_	_	20		
	GZ47A	П			T2 (+) , Gate (−)	-	_	20		
	SM12	M12JZ47A	Ш			T2 (-) , Gate (-)	_	_	20	-
			IV			T2 (-) , Gate (+)	_	_	_	
Peak On-State Voltage			V _{TM}	I _{TM} = 17A			_	1.5	V	
Gate Non-Trigge	Gate Non-Trigger Voltage		V _{GD}	V _D = Rated, Tc = 125°C		0.2	_	_	V	
Holding Current				Ι _Η	V _D = 12V, I _{TM} = 1A			_	50	mA
Thermal Resistar	-			R _{th (j−c)}	Junction to Case, AC			_	3.0	°C/W
Critical Rate of Rise of Off-State		SM12GZ47 SM12JZ47		dv / dt	V _{DRM} = Rated, T _i = 125°C		_	300	_	V/µs
Voltage	SM12GZ47 SM12JZ47		Exponential R		e	_	200	_	v / µə	
Critical Rate of Rise of Off-State)	SM12GZ4 SM12JZ47		(dv / dt) c	V _{DRM} = 400V, 1	「 _i = 125°C	10	_		
		SM12GZ47 SM12JZ47			(di / dt) c = - 6.5A / ms		4	_	_	v/µs

MARKING

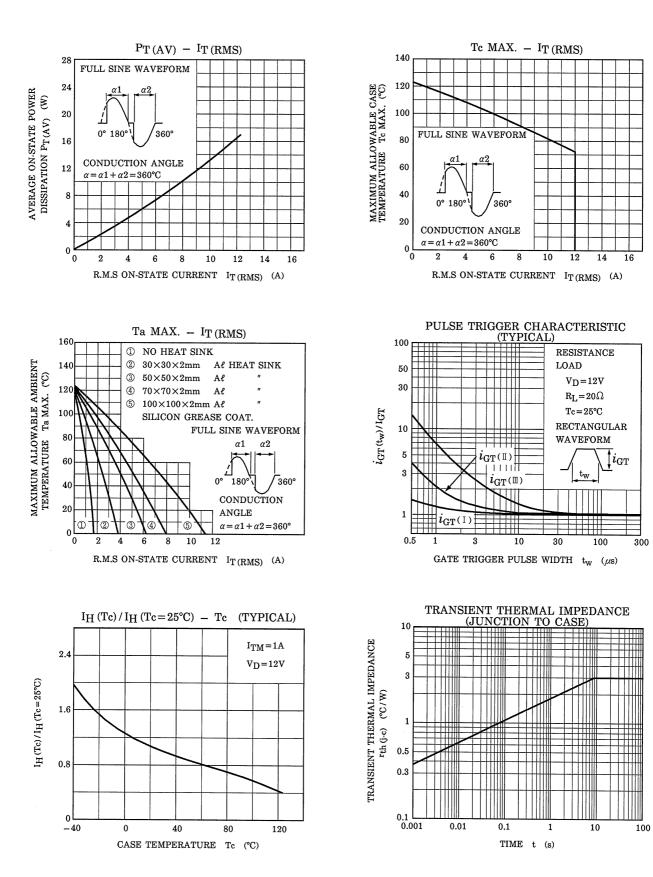
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*NUMBER	SYMBOL		MARK	
*1	TOSHIBA PRODUCT MARK		5	
*2		SM12GZ47, SM12GZ47A	M12GZ47	
2	TYPE	SM12JZ47, SM12JZ47A	M12JZ47	
*3		SM12GZ47A, SM12JZ47A	A	
*4		(Starting from Alphabet A) (Last Decimal Digit of the Current Year)	Example 8A: January 1998 8B: February 1998 8L: December 1998	



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